Transistors Panasonic

2SC6054J

Silicon NPN epitaxial planar type

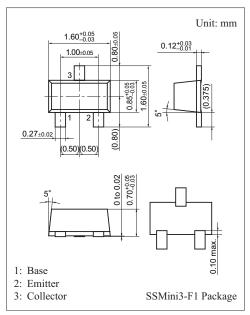
For general amplification Complementary to 2SA2174J

■ Features

- High forward current transfer ratio h_{FE}
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter | Symbol | Rating | Unit | |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | V _{CBO} | 60 | V | |
| Collector-emitter voltage (Base open) | V _{CEO} | 50 | V | |
| Emitter-base voltage (Collector open) | V _{EBO} | 7 | V | |
| Collector current | I_{C} | 100 | mA | |
| Peak collector current | I _{CP} | 200 | mA | |
| Collector power dissipation | P _C | 125 | mW | |
| Junction temperature | T _j | 125 | °C | |
| Storage temperature | T _{stg} | -55 to +125 | °C | |



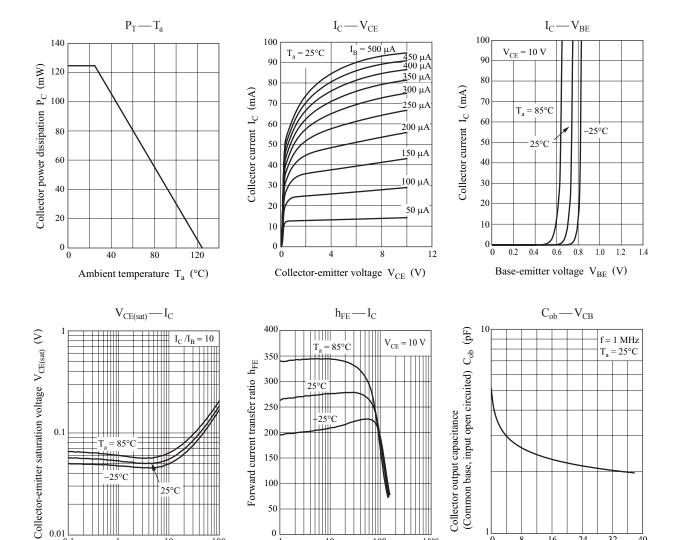
Marking Symbol: 7M

■ Electrical Characteristics $T_a = 25$ °C±3°C

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------------------|---|-----|-----|-----|------|
| Collector-base voltage (Emitter open) | V _{CBO} | $I_C = 10 \mu A, I_E = 0$ | 60 | | | V |
| Collector-emitter voltage (Base open) | V _{CEO} | $I_C = 2 \text{ mA}, I_B = 0$ | 50 | | | V |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_E = 10 \mu A, I_C = 0$ | 7 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 20 \text{ V}, I_{E} = 0$ | | | 0.1 | μА |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{CE} = 10 \text{ V}, I_{B} = 0$ | | | 100 | μА |
| Forward current transfer ratio | h_{FE} | $V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$ | 160 | | 460 | _ |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$ | | 0.1 | 0.3 | V |
| Transition frequency | f_T | $V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$ | | 100 | | MHz |
| Collector output capacitance (Common base, input open circuited) | C _{ob} | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | | 2.2 | | pF |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Panasonic 2SC6054J



100

Collector current I_C (mA)

1000

Collector-base voltage V_{CB} (V)

50

2 SJC00343AED

Collector current I_C (mA)

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